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Substitute for form 1448A/B/PTO			Complete if Known		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	10/663,741	
			Filing Date	September 17, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	1	of	1	Attorney Docket Number	M4065.0656/P656

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
<i>CG</i>	A	6,673,648	01/06/2004	Lowrey	

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Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ³
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)				

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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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Art Unit	N/A
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U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ¹ (if known)			
Ch	AA	2002/0000666	1/3/2002	Kozicki et al.	
Ch	AB	2002/0072188	6/13/2002	Gilton	
Ch	AC	2002/0106849	08/08/2002	Moore	
Ch	AH	2002/0123169	09/05/2002	Moore et al.	
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Ch	AL	2002/0132417	09/09/2002	Li	
Ch	AF	2002/0160551	10/31/2002	Harshfield	
Ch	AG	2002/0163828	11/07/2002	Krieger et al.	
Ch	AM	2002/0168820	11/2002	Kozicki	
Ch	AN	2002/0168852	11/14/2002	Harshfield et al.	
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Ch	AT	2003/0035314	02/20/2003	Kozicki	
Ch	AU	2003/0035315	02/20/2003	Kozicki	
Ch	AV	2003/0038301	02/27/2003	Moore	
Ch	AW	2003/0043631	03/06/2003	Gilton et al.	
Ch	AX	2003/0045049	03/06/2003	Campbell et al.	
Ch	AY	2003/0045054	03/06/2003	Campbell et al.	
Ch	AZ	2003/0047765	03/13/2003	Campbell	
Ch	AA1	2003/0047772	03/13/2003	Li	
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Ch	AC1	2003/0048519	03/13/2003	Kozicki	
Ch	AD1	2003/0049912	03/13/2003	Campbell et al.	
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Ch	AG1	2003/0095426	05/22/2003	Hush et al.	
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Ch	AM1	2003/0143782	07/31/2003	Gilton et al.	
Ch	AN1	2003/0155589	08/21/2003	Campbell et al.	
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Ch	AT1	4,269,935	5/1981	Masters et al.	

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Ch	AU1	4,312,938	1/1982	Drexler, et al.
Ch	AV1	4,316,946	1/1982	Masters, et al.
Ch	AW1	4,320,191	3/1982	Yoshikawa et al.
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Ch	AP3	6,348,365	2/19/2002	Moore et al.
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 Sheet **3** of **11**

<input checked="" type="checkbox"/>	AR3	6,376,284	4/2002	Gonzalez et al.		
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<input checked="" type="checkbox"/>	AV3	6,418,049	7/9/2002	Kozicki et al.		
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<input checked="" type="checkbox"/>	AX3	6,423,628	7/2002	Li et al.		
<input checked="" type="checkbox"/>	AY3	6,440,837	8/27/2002	Harshfield		
<input checked="" type="checkbox"/>	AZ3	6,469,364	10/2002	Kozicki		
<input checked="" type="checkbox"/>	AA4	6,473,332	10/2002	Ignatiev et al.		
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<input checked="" type="checkbox"/>	AC4	2003/0209728	11/13/2003	Kozicki et al.		
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<input checked="" type="checkbox"/>	AF4	2002/0101765	08/01/2002	Mihnea et al.		
<input checked="" type="checkbox"/>	AG4	6,426,898	07/30/2002	Mihnea et al.		
<input checked="" type="checkbox"/>	AH4	2002/0130351	09/19/2002	Ghods		
<input checked="" type="checkbox"/>	AJ4	2002/0159292	10/31/2002	Forbes		
<input checked="" type="checkbox"/>	AJ4	5,534,712	07/09/1998	Ovshinsky et al.		
<input checked="" type="checkbox"/>	AK4	2002/0163030	11/07/2002	Mandell et al.		
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<input checked="" type="checkbox"/>	BA	56126916	10/19981	Akira et al.		
<input checked="" type="checkbox"/>	BB	WO 97/48032	12/18/1997	Kozicki et al.		
<input checked="" type="checkbox"/>	BC	WO 99/28914	06/10/1999	Kozicki et al.		
<input checked="" type="checkbox"/>	BD	WO 00/48196	08/17/2000	Kozicki et al.		
<input checked="" type="checkbox"/>	BE	WO 02/21542	03/14/2002	Kozicki et al.		

Examiner Signature	<i>[Signature]</i>	Date Considered	12-12-04
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Sheet	4	of	11	Application Number	10/663,741
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
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an	CB	Adler, D.; Moss, S.C., Amorphous memories and bistable switches, J. Vac. Sci. Technol. 9 (1972) 1182-1189.	
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Sheet	5	of	11
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cn	CW	Bondarev, V.N.; Pikhitsa, P.V., A dendrite model of current instability in RbAg4I5, Solid State Ionics 70/71 (1994) 72-76.	
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CU1	dan Boer, W., Threshold switching in hydrogenated amorphous silicon, Appl. Phys. Lett. 40 (1982) 812-813.		
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CW1	El Bouchairi, B.; Bernede, J.C.; Burgaud, P., Properties of Ag ₂ -xSe _{1+x/n} -Si diodes, Thin Solid Films 110 (1983) 107-113.		
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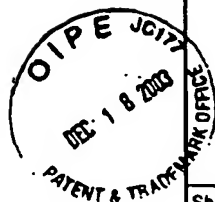
Sheet	7	of	11	Attorney Docket Number	M4065.0656/P656
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Examiner Signature	<i>[Signature]</i>	Date Considered	12-12-04
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				Application Number	10/663,741-Conf. #2658
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0656/P656

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			

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an	CA	YOJI KAWAMOTO et al., "Ionic Conduction in As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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Handwritten signature: J. Gilton
Handwritten date: 12-12-04



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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Application Number	10/663,741
		Filing Date	September 17, 2003
		First Named Inventor	Terry L. Gilton
		Art Unit	2811
		Examiner Name	Not Yet Assigned
Sheet	1	of	3
		Attorney Docket Number	M4065.0656/P656

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		Number-Kind Code ² (if known)			
CA	A	US 2004/0035401	2/2004	Ramachandran et al.	
CA	B	US 2003/0212724	11/2003	Ovshinsky et al.	
CA	C	US 2003/0048744	3/2003	Ovshinsky et al.	
CA	D	US 2003/0212725	11/2003	Ovshinsky et al.	
CA	E	US RE 37,259E	7/2001	Ovshinsky	
CA	F	US 3,271,591	9/1966	Ovshinsky	
CA	G	US 3,961,314	6/1976	Klose et al.	
CA	H	US 3,966,317	6/1976	Wacks et al.	
CA	I	US 3,983,542	11/1976	Ovshinsky	
CA	J	US 3,988,720	10/1976	Ovshinsky	
CA	K	US 4,177,474	12/1979	Ovshinsky	
CA	L	US 4,267,261	5/1981	Hallman et al.	
CA	M	US 4,597,162	7/1986	Johnson et al.	
CA	N	US 4,608,296	8/1986	Keem et al.	
CA	O	US 4,637,895	1/1987	Ovshinsky et al.	
CA	P	US 4,646,266	2/1987	Ovshinsky et al.	
CA	Q	US 4,664,939	5/1987	Ovshinsky	
CA	R	US 4,668,968	5/1987	Ovshinsky et al.	
CA	S	US 4,670,763	6/1987	Ovshinsky et al.	
CA	T	US 4,673,957	6/1987	Ovshinsky et al.	
CA	U	US 4,678,679	7/1987	Ovshinsky	
CA	V	US 4,696,758	9/1987	Ovshinsky et al.	
CA	W	US 4,698,234	10/1987	Ovshinsky et al.	
CA	X	US 4,710,899	12/1987	Young et al.	
CA	Y	US 4,728,406	3/1988	Banerjee et al.	
CA	Z	US 4,737,379	4/1988	Hudgens et al.	
CA	A1	US 4,766,471	8/1988	Ovshinsky et al.	
CA	B1	US 4,769,338	9/1988	Ovshinsky et al.	
CA	C1	US 4,775,425	10/1988	Guha et al.	
CA	D1	US 4,788,594	11/1988	Ovshinsky et al.	
CA	E1	US 4,809,044	2/1989	Pryor et al.	
CA	F1	US 4,818,717	4/1989	Johnson et al.	
CA	G1	US 4,843,443	6/1989	Ovshinsky et al.	
CA	H1	US 4,845,533	7/1989	Pryor et al.	
CA	I1	US 4,853,785	8/1989	Ovshinsky et al.	
CA	J1	US 4,891,330	1/1990	Guha et al.	
CA	K1	US 5,128,099	7/1992	Strand et al.	
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CA	N1	US 5,177,567	1/1993	Kiersy et al.	
CA	O1	US 5,296,716	3/1994	Ovshinsky et al.	
CA	P1	US 5,335,219	8/1994	Ovshinsky et al.	
CA	Q1	US 5,359,205	10/1994	Ovshinsky	
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			Filing Date	September 17, 2003	
			First Named Inventor	Terry L. Gilton	
			Art Unit	2811	
			Examiner Name	Not Yet Assigned	
Sheet	2	of	3	Attorney Docket Number	M4065.0656/P656

OK	T1	US 5,414,271	5/1995	Ovshinsky et al.	
OK	U1	US 5,534,711	7/1996	Ovshinsky et al.	
OK	V1	US 5,534,712	7/1996	Ovshinsky et al.	
OK	W1	US 5,536,947	7/1996	Klersy et al.	
OK	X1	US 5,543,737	8/1996	Ovshinsky	
OK	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
OK	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
OK	A2	US 5,687,112	11/1997	Ovshinsky	
OK	B2	US 5,694,054	12/1997	Ovshinsky et al.	
OK	C2	US 5,714,768	2/1998	Ovshinsky et al.	
OK	D2	US 5,825,046	10/1998	Czubatyj et al.	
OK	E2	US 5,912,839	8/1999	Ovshinsky et al.	
OK	F2	US 5,933,365	8/1999	Klersy et al.	
OK	G2	US 6,011,757	1/2000	Ovshinsky	
OK	H2	US 6,087,674	7/2000	Ovshinsky et al.	
OK	I2	US 6,141,241	10/2000	Ovshinsky et al.	
OK	J2	US 6,339,544	1/2002	Chiang et al.	
OK	K2	US 6,404,665	6/2002	Lowery et al.	
OK	L2	US 6,429,064	8/2002	Wicker	
OK	M2	US 6,437,383	8/2002	Xu	
OK	N2	US 6,462,984	10/2002	Xu et al.	
OK	O2	US 6,480,438	11/2002	Park	
OK	P2	US 6,487,113	11/2002	Park et al.	
OK	Q2	US 6,501,111	12/2002	Lowery	
OK	R2	US 6,507,061	1/2003	Hudgens et al.	
OK	S2	US 6,511,862	1/2003	Hudgens et al.	
OK	T2	US 6,511,867	1/2003	Lowery et al.	
OK	U2	US 6,512,241	1/2003	Lai	
OK	V2	US 6,514,805	2/2003	Xu et al.	
OK	W2	US 6,531,373	3/2003	Gill et al.	
OK	X2	US 6,534,781	3/2003	Dennison	
OK	Y2	US 6,545,287	4/2003	Chiang	
OK	Z2	US 6,545,907	4/2003	Lowery et al.	
OK	A3	US 6,555,860	4/2003	Lowery et al.	
OK	B3	US 6,563,164	5/2003	Lowery et al.	
OK	C3	US 6,566,700	5/2003	Xu	
OK	D3	US 6,567,293	5/2003	Lowery et al.	
OK	E3	US 6,569,705	5/2003	Chiang et al.	
OK	F3	US 6,570,784	5/2003	Lowery	
OK	G3	US 6,576,921	6/2003	Lowery	
OK	H3	US 6,586,761	7/2003	Lowery	
OK	I3	US 6,589,714	7/2003	Maimon et al.	
OK	J3	US 6,590,807	7/2003	Lowery	
OK	K3	US 6,593,176	7/2003	Dennison	
OK	L3	US 6,597,009	7/2003	Wicker	
OK	M3	US 6,605,527	8/2003	Dennison et al.	
OK	N3	US 6,613,604	9/2003	Maimon et al.	
OK	O3	US 6,621,095	9/2003	Chiang et al.	
OK	P3	US 6,625,054	9/2003	Lowery et al.	
OK	Q3	US 6,642,102	11/2003	Xu	

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Sheet	3	of	3	Attorney Docket Number	M4065.0656/P656

<i>Ch</i>	R3	US 6,646,297	11/2003	Dennison	
<i>Ch</i>	S3	US 6,649,928	11/2003	Dennison	
<i>Ch</i>	T3	US 6,667,900	12/2003	Lowery et al.	
<i>Ch</i>	U3	US 6,671,710	12/2003	Ovshinsky et al.	
<i>Ch</i>	V3	US 6,673,700	1/2004	Dennison et al.	
<i>Ch</i>	W3	US 6,674,115	1/2004	Hudgens et al.	
<i>Ch</i>	X3	US 6,687,427	2/2004	Ramalingam et al.	
<i>Ch</i>	Y3	US 6,690,026	2/2004	Peterson	
<i>Ch</i>	Z3	US 6,696,355	2/2004	Dennison	
<i>Ch</i>	A4	US 6,687,153	2/2004	Lowery	
<i>Ch</i>	B4	US 6,707,712	3/2004	Lowery	
<i>Ch</i>	C4	US 6,714,954	3/2004	Ovshinsky et al.	

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